

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL60B** is Designed for

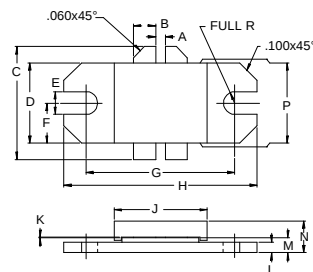
FEATURES:

- Input Matching Network
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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CBO}	60 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	146 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	$-65\text{ }^{\circ}\text{C}$ to $+200\text{ }^{\circ}\text{C}$
T_{STG}	$-65\text{ }^{\circ}\text{C}$ to $+150\text{ }^{\circ}\text{C}$
θ_{JC}	1.2 $^{\circ}\text{C/W}$

PACKAGE STYLE .450 BAL FLG (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.055 / 1.40
B	.120 / 3.05	.130 / 3.30
C		.785 / 19.94
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F		.230 / 5.84
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N		.195 / 4.95
P	.445 / 11.30	.455 / 11.56

ORDER CODE: ASI10584

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100\text{ mA}$	60			V
BV_{CEO}	$I_C = 100\text{ mA}$	28			V
BV_{EBO}	$I_E = 20\text{ mA}$	3.5			V
I_{CEO}	$V_{CE} = 25\text{ V}$			30	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 3.0\text{ A}$	25		80	---
P_G	$V_{CC} = 26\text{ V}$ $I_{CQ} = 2 \times 200\text{ mA}$ $f = 960\text{ MHz}$ $P_{OUT} = 60\text{ W}$	8.5			dB
VSRW	$V_{CC} = 26\text{ V}$ $f = 960\text{ MHz}$	5:1			---